

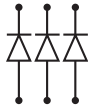
CMKD6001

**SURFACE MOUNT
TRIPLE ISOLATED
ULTRA LOW LEAKAGE
SILICON SWITCHING DIODES**



www.centrasemi.com

ULTRAmulti™



SOT-363 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMKD6001 type contains three (3) Isolated Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a ULTRAmulti™ surface mount package, designed for switching applications requiring extremely low leakage.

MARKING CODE: K01

MAXIMUM RATINGS: (T_A=25°C)

Continuous Reverse Voltage	
Peak Repetitive Reverse Voltage	
Continuous Forward Current	
Peak Repetitive Forward Current	
Peak Forward Surge Current, tp=1.0µs	
Peak Forward Surge Current, tp=1.0s	
Power Dissipation	
Operating and Storage Junction Temperature	
Thermal Resistance	

SYMBOL

V _R	75
V _{RRM}	100
I _F	250
I _{FRM}	500
I _{FSM}	4.0
I _{FSM}	1.0
P _D	250
T _J , T _{stg}	-65 to +150
θ _{JA}	500

UNITS

V
V
mA
mA
A
A
mW
°C
°C/W

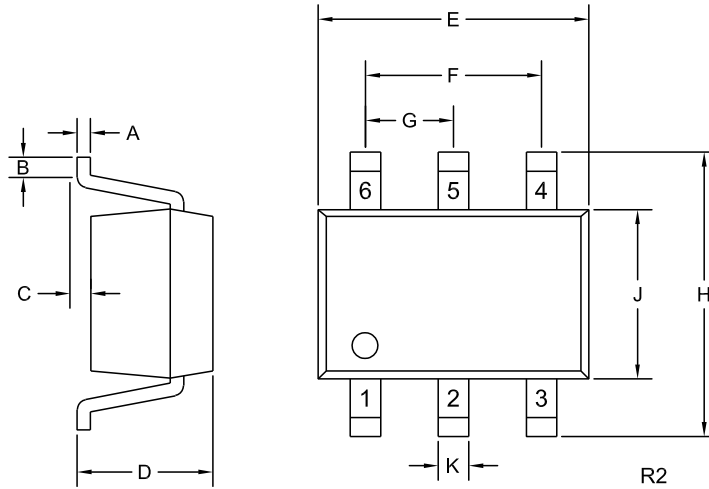
ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _R	V _R =75V		500	pA
BV _R	I _R =100µA	100		V
V _F	I _F =1.0mA		0.85	V
V _F	I _F =10mA		0.95	V
V _F	I _F =100mA		1.1	V
C _T	V _R =0, f=1.0MHz		2.0	pF
t _{rr}	I _R =I _F =10mA, I _{rr} =1.0mA, R _L =100Ω		3.0	µs

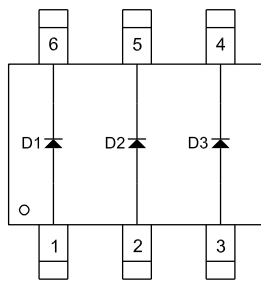
CMKD6001
SURFACE MOUNT
TRIPLE ISOLATED
ULTRA LOW LEAKAGE
SILICON SWITCHING DIODES



SOT-363 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



LEAD CODE:

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1

MARKING CODE: K01

SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.010	0.10	0.25
B	0.005	-	0.12	-
C	0.000	0.004	0.00	0.10
D	0.031	0.043	0.80	1.10
E	0.071	0.087	1.80	2.20
F	0.051		1.30	
G	0.026		0.65	
H	0.075	0.091	1.90	2.30
J	0.043	0.055	1.10	1.40
K	0.006	0.012	0.15	0.30

SOT-363 (REV: R2)

R5 (9-May 2011)